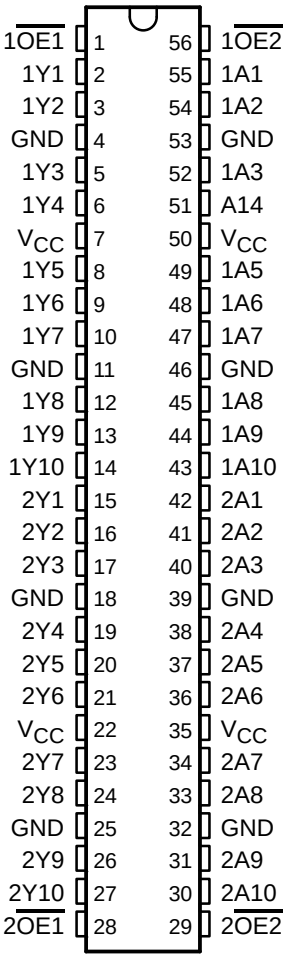
- **Output Ports Have Equivalent 25-Ω Series Resistors, So No External Resistors Are Required**
- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art *EPIC*-II*B*™ BiCMOS Design Significantly Reduces Power Dissipation**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Typical V_{OLP} (Output Ground Bounce) < 1 V at V_{CC} = 5 V, T_A = 25°C**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54ABT162827 . . . WD PACKAGE
SN74ABT162827 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The ′ABT162827 are noninverting 20-bit buffers composed of two 10-bit buffers with separate output-enable signals. For either 10-bit buffer, the two output-enable (1$\overline{OE1}$ and 1$\overline{OE2}$ or 2$\overline{OE1}$ and 2$\overline{OE2}$) inputs must both be low for the corresponding Y outputs to be active. If either output-enable input is high, the outputs of that 10-bit buffer are in the high-impedance state.

The outputs, which are designed to source or sink up to 12 mA, include 25-Ω series resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ inputs should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ABT162827 is available in TI's shrink small-outline package (DL), which provides twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54ABT162827 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABT162827 is characterized for operation from –40°C to 85°C.

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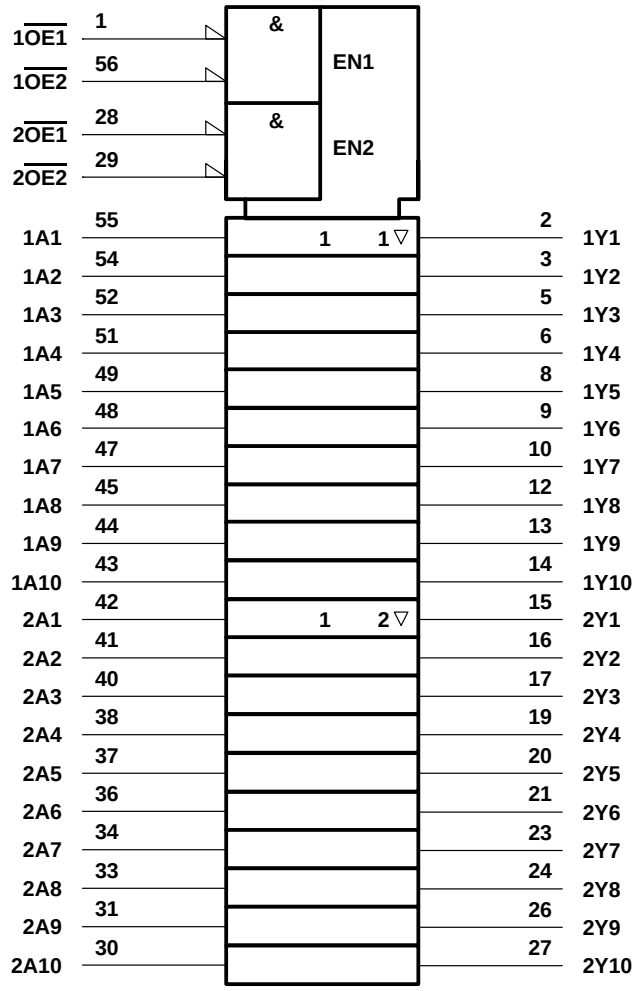
FUNCTION TABLE
(each 10-bit buffer)

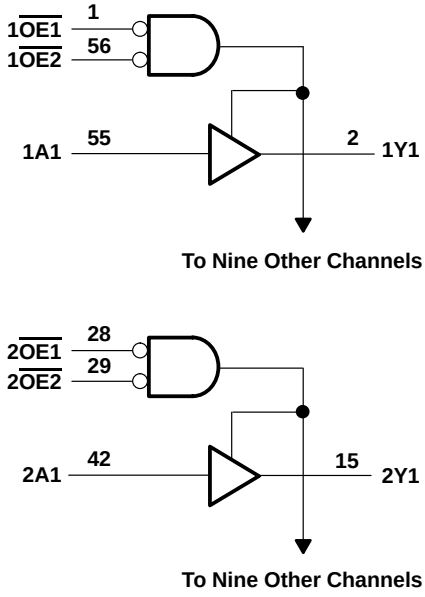
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O . . . . . –0.5 V to 5.5 V
Current into any output in the low state, I_O . . . . . 30 mA
Input clamp current, I_{IK} (V_I < 0) . . . . . –18 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 2): DGG package . . . . . 1 W
DL package . . . . . 1.4 W
Operating free-air temperature range, T_A: SN54ABT162827 . . . . . –55°C to 125°C
SN74ABT162827 . . . . . –40°C to 85°C
Storage temperature range . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 3)

			SN54ABT162827		SN74ABT162827		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current			–12		–12	mA
I_{OL}	Low-level output current			12		12	mA
$\Delta t/\Delta V$	Input transition rise or fall rate	Control inputs		9		9	ns/V
		Data inputs		10		10	
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 3: Unused or floating inputs must be held high or low.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A = 25°C			SN54ABT162827		SN74ABT162827		UNIT
				MIN	TYP†	MAX	MIN	MAX	MIN	MAX	
V_{IK}		V_{CC} = 4.5 V,	I_I = –18 mA			–1.2		–1.2		–1.2	V
V_{OH}		V_{CC} = 4.5 V,	I_{OH} = – 1 mA	2.5			2.5		2.5		V
		V_{CC} = 5 V,	I_{OH} = – 1 mA	3			3		3		
		V_{CC} = 4.5 V	I_{OH} = – 3 mA	2.4			2.4		2.4		
			I_{OH} = – 12 mA	2			2		2		
V_{OL}		V_{CC} = 4.5 V	I_{OL} = 8 mA		0.4	0.8		0.8		0.65	V
			I_{OL} = 12 mA							0.8	
I_I		V_{CC} = 0 to 5.5 V, V_I = V_{CC} or GND				±1		±1		±1	µA
I_{OZPU}		V_{CC} = 0 to 2.1 V, V_O = 0.5 V to 2.7 V,	$\overline{OE}$ = X			±50		±50		±50	µA
I_{OZPD}		V_{CC} = 2.1 V to 0, V_O = 0.5 V to 2.7 V,	$\overline{OE}$ = X			±50		±50		±50	µA
I_{OZH}‡		V_{CC} = 2.1 V to 5.5 V, V_O = 2.7 V,	$\overline{OE}$ ≥ 2 V			10		10		10	µA
I_{OZL}‡		V_{CC} = 2.1 V to 5.5 V, V_O = 0.5 V,	$\overline{OE}$ ≥ 2 V			–10		–10		–10	µA
I_{off}		V_{CC} = 0,	V_I or V_O ≤ 4.5 V			±100				±100	µA
I_{CEX}	Outputs high	V_{CC} = 5.5 V,	V_O = 5.5 V			50		50		50	µA
I_O§		V_{CC} = 5.5 V,	V_O = 2.5 V	–25	–75	–100	–25	–100	–25	–100	mA
I_{CC}	Outputs high	V_{CC} = 5.5 V, V_I = V_{CC} or GND	I_O = 0,			2		2		2	mA
	Outputs low					32		32		32	
	Outputs disabled					2		2		2	
ΔI_{CC}¶	Data inputs	V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND	Outputs enabled			1		1.5		1	mA
			Outputs disabled			0.05		1		0.05	
	Control inputs	V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND				1.5		1.5		1.5	
C_i		V_I = 2.5 V or 0.5 V			3.5						pF
C_o		V_O = 2.5 V or 0.5 V			8						pF

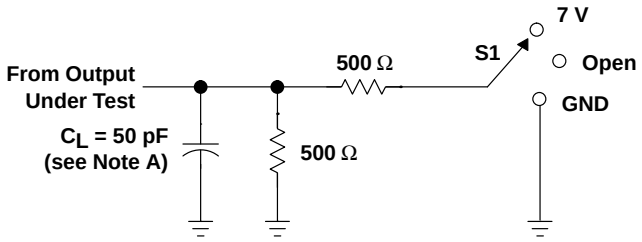
† All typical values are at V_{CC} = 5 V.
‡ The parameters I_{OZH} and I_{OZL} include the input leakage current.
§ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 5 V, T_A = 25°C			SN54ABT162827		SN74ABT162827		UNIT
			MIN	TYP†	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	Y	1	2.1	3.6	1	4.1	1	3.9	ns
t_{PHL}			1.1	2.8	4.2	1.1	5	1.1	4.7	
t_{PZH}	$\overline{OE}$	Y	1.5	3.4	6.3	1.5	7.2	1.5	6.9	ns
t_{PZL}			1.6	3.5	7.3	1.6	6.6	1.6	6.3	
t_{PHZ}	$\overline{OE}$	Y	2.1	4.1	6.5	2.1	6.8	2.1	6.6	ns
t_{PLZ}			1.5	3.5	5.9	1.5	7.3	1.5	6.3	

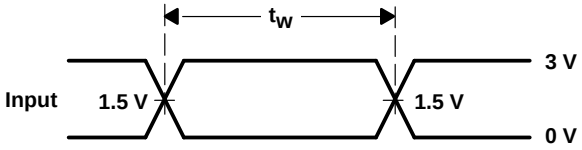
† All typical values are at V_{CC} = 5 V.

PARAMETER MEASUREMENT INFORMATION

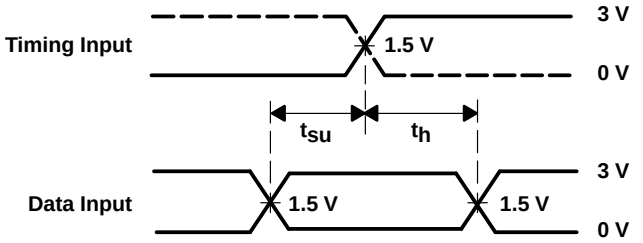


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open

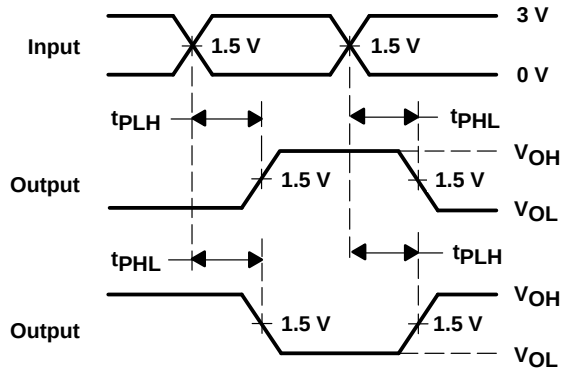
LOAD CIRCUIT FOR OUTPUTS



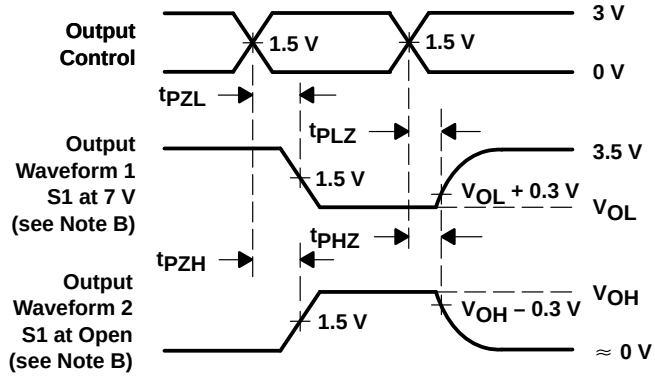
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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